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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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**Micro Commercial Components** 

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## TSMBJ1006C THRU TSMBJ1024C

### **Features**

- Oxide-Glass passivated Junction
- Bi-Directional protection in a single device
- Surge capabilities up to 100A@10/1000us or 400A@8/20us
- High Off-State impedance and Low On-State voltage
- Plastic material has UL flammability classification 94V-0

# Transient Voltage Protection Device 75 to 320 Volts

### **Mechanical Data**

· Case : Molded plastic

• Polarity : None cathode band denotes

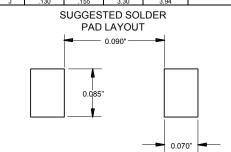
Approx Weight: 0.093grams

### **Maximum Rating**

Characteristic	Symbol	Value	Unit
Non-repetitive peak impulse current	l <sub>PP</sub>	100A	10/1000us
Non-repetitive peak On-state current	I <sub>TSM</sub>	50A	8.3ms, one-half cycle
Operating temperature range	$T_{OP}$	-40~150°C	•
Junction and storage temperature range	$T_J$ , $T_{STG}$	-55~150°C	

# DO-214AA (SMBJ) A A C DIMENSIONS

DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
Α	.078	.096	2.00	2.44	
В	.077	.083	1.96	2.10	
С	.002	.008	.05	.20	
D		.02		.51	
E	.030	.060	.76	1.52	
F	.065	.091	1.65	2.32	
G	.205	.220	5.21	5.59	
Н	.160	.180	4.06	4.57	
J	.130	.155	3.30	3.94	
<u> </u>	SUGGESTED SOLDER				



### **Thermal Resistance**

Characteristic	Symbol	Value	Unit
Thermal Resistance junction to lead	$R_{ heta JL}$	20°C/W	
Thermal Resistance junction to ambient	$R_{\theta JA}$	100°C/W	On recommended pad layout
Typical positive temperature coefficient for breakdown voltage	∆V <sub>BR</sub> /∆T <sub>J</sub>	0.1%/℃	

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### TSMBJ1006C thru TSMBJ1024C



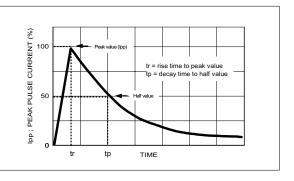
**Micro Commercial Components** 

### ELECTRICAL CHARACTERISTIC @25°C Unless otherwise specified

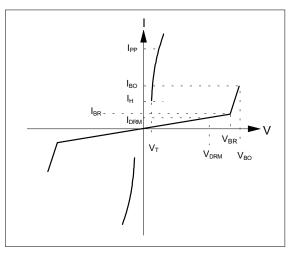
Parameter	Rated Repetitive Off- state Voltage	Off-state Leakage Current@V <sub>DRM</sub>	Breakover Voltage	On-State Voltage @I <sub>r</sub> =1.0A	Breakover Current	Holding Current	Off-State
Symbol	$V_{DRM}$	I <sub>DRM</sub>	$V_{BO}$	V <sub>T</sub>	I <sub>BO+</sub>	I <sub>H</sub>	C <sub>J</sub>
Units	Volts	uA	Volts	Volts	mA	mA	pF
Limit	Max	Max	Max	Max	Max	Min	Тур.
TSMBJ1006C	75	5	98	5	800	150	200
TSMBJ1007C	90	5	130	5	800	150	120
TSMBJ1010C	140	5	180	5	800	150	120
TSMBJ1012C	160	5	220	5	800	150	120
TSMBJ1016C	190	5	265	5	800	150	80
TSMBJ1018C	220	5	300	5	800	150	80
TSMBJ1022C	275	5	350	5	800	150	80
TSMBJ1024C	320	5	400	5	800	150	80

### **MAXIMUM RATED SURGE WAVEFORM**

<u> </u>					
Standard	lpp (A)				
GR-1089-CORE	500				
IEC 61000-4-5	400				
FCC Part 68	200				
ITU-T K20/21	200				
FCC Part 68	150				
GR-1089-CORE	100				
	Standard GR-1089-CORE IEC 61000-4-5 FCC Part 68 ITU-T K20/21 FCC Part 68				



Symbol	Parameter
$V_{DRM}$	Stand-off voltage
I <sub>DRM</sub>	Leakage current at stand-off voltage
$V_{BR}$	Breakdown voltage
I <sub>BR</sub>	Breakdown current
V <sub>BO</sub>	Breakover voltage
I <sub>BO</sub>	Breakover current
I <sub>H</sub>	Holding current NOTE: 1
V <sub>T</sub>	On state voltage
I <sub>PP</sub>	Peak pulse current
Co	Off-state capacitance NOTE: 2



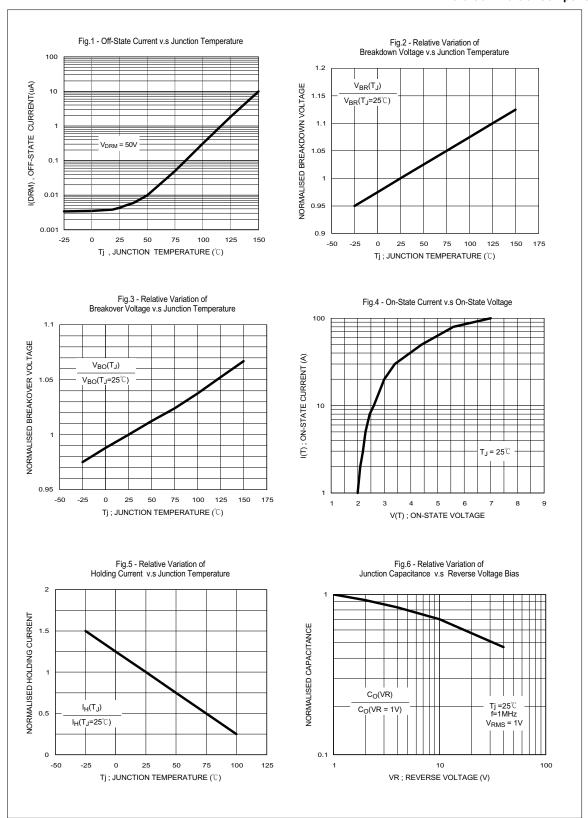
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<sup>1.</sup> I  $_{H}$  > (  $_{V}$   $_{L}$  /  $_{R}$   $_{L}$ ) If this criterion is not obeyed, the TSPD triggers but does not return correctly to high-resistance state. The surge recovery time. It does not exceed 30ms.

2. Off-state capacitance measured at f=1.0MHz , 1.0Vrms signal , VR=2Vdc bias.



### TSMBJ1006C thru TSMBJ1024C



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### TSMBJ1006C thru TSMBJ1024C

# **Micro Commercial Components** TYPICAL APPLICATION CIRCUITS FUSE RING -TELECOM TVPD 1 **EQUIPMENT** E.G. MODEM RING PTC **TELECOM EQUIPMENT** E.G. ISDN RING -TELECOM **EQUIPMENT** E.G. LINE CARD

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The PTC (Positive Temperature Coefficient) is an overcurrent protection device.

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### **MARKING CODE**

